IN THE CLAIMS:

Please amend the claims as follows:

1 (Currently amended). A cleaning or photoresist stripping composition comprising:

(a) from about 5% to about 50% by weight of a polar aprotic nitrogen-containing solvent having a dipole moment of more than about 3.5;

(b) from about 0.2% to about 20% by weight of a compound ~~choline derivative~~ selected from the group consisting of a hydroxide and/or salt of bis-(2-hydroxy-ethyl)-dimethyl ammonium, a hydroxide and/or salt of tris-(2-hydroxy-ethyl)-methyl ammonium, ~~bis-choline salt, a tris-choline salt~~, and a mixture thereof; and

(c) from about 50% to about 94% by weight of a sulfur-containing solvent selected from the group consisting of a sulfoxide, a sulfone, and a mixture thereof , wherein the composition is substantially free of hydroxylamine.

2 (previously presented). The composition of claim 1, wherein the polar aprotic nitrogen-containing solvent comprises N methyl 2 pyrrolidone.

3 (previously presented). The composition of claim 1, wherein the polar aprotic nitrogen-containing solvent is present in an amount from about 15% to about 35% by weight,

4 (previously presented). The composition of claim 3, wherein the polar aprotic nitrogen-containing solvent is present in an amount from about 20% to about 30% by weight.

5 (previously presented). The composition of claim 4, wherein the polar aprotic nitrogen-containing solvent is present in an amount from about 24% to about 26% by weight.

6 (Currently amended). The composition of claim 1, wherein the hydroxide and/or salt of bis-(2-hydroxy-ethyl)-dimethyl ammonium, a hydroxide and/or salt of tris-(2-hydroxy-ethyl)-methyl ammonium, or mixture thereof ~~choline derivative~~ is present in an amount

from about 0.5% to about 10% by weight.

7 (Currently amended). The composition of claim 6, wherein the hydroxide and/or salt of bis-(2-hydroxy-ethyl)-dimethyl ammonium, a hydroxide and/or salt of tris-(2-hydroxy-ethyl)-methyl ammonium, or mixture thereof ~~choline derivative~~ is present in an amount from about 1% to about 5% by weight.

8 (Currently amended). The composition of claim 7, wherein the hydroxide and/or salt of bis-(2-hydroxy-ethyl)-dimethyl ammonium, a hydroxide and/or salt of tris-(2-hydroxy-ethyl)-methyl ammonium, or mixture thereof ~~choline derivative~~ is present in an amount from about 1% to about 3% by weight.

9 (previously presented). The composition of claim 1, wherein the sulfur-containing solvent comprises dimethyl sulfoxide, methyl sulfoxide, or a mixture thereof.

10 (previously presented). The composition of claim 9, wherein the sulfur-containing solvent is present in an amount from about 60% to about 84% by weight.

11 (previously presented). The composition of claim 10, wherein the sulfur-containing solvent is present in an amount from about 66% to about 76% by weight.

12 (previously presented). The composition of claim 11, wherein the sulfur-containing solvent is present in an amount from about 70% to about 72% by weight.

13 (previously presented). The composition of claim 1, which is further substantially free of water.

14 (previously presented). The composition of claim 1, which is further substantially free of one or more of the following: additional amines, additional corrosion inhibitors, additional chelating agents, additional surfactants, additional organic solvents, additional acids, and additional bases.

15 (cancelled).

16 (previously presented). The composition of claim 1, further comprising up to about 10% by weight of water.

17 (previously presented). A cleaning or photoresist stripping composition consisting essentially of:

(a) from about 5% to about 50% by weight of a polar aprotic nitrogen-containing solvent having a dipole moment of more than about 3.5;

(b) from about 0.2% to about 20% by weight of a choline derivative selected from the group consisting of a bis-choline salt, a tris-choline salt, and a mixture thereof; and

(c) from about 50% to about 94% by weight of a sulfur-containing solvent selected from the group consisting of a sulfoxide, a sulfone, and a mixture thereof.

18 (Currently amended). The composition of claim 17, wherein the polar aprotic nitrogen-containing solvent comprises ~~N-methyl-2-pyrrolidone~~ N-methyl-2-pyrrolidone.

19 (previously presented). The composition of claim 17, wherein the polar aprotic nitrogen-containing solvent is present in an amount from about 15% to about 35% by weight.

20 (previously presented). The composition of claim 19, wherein the polar aprotic nitrogen-containing solvent is present in an amount from about 20% to about 30% by weight.

21 (Currently amended). The composition of claim 17, wherein the choline derivative is present in an amount from about 0.5% to about 10% by weight.

22 (Currently amended). The composition of claim 21, wherein the choline derivative is present in an amount from about 1% to about 5% by weight.

23 (previously presented). The composition of claim 17, wherein the sulfur-containing solvent comprises dimethyl sulfoxide, methyl sulfoxide, or a mixture thereof.

24 (previously presented). The composition of claim 23, wherein the sulfur-containing solvent is present in an amount from about 60% to about 84% by weight.

25 (previously presented). The composition of claim 24, wherein the sulfur-containing solvent is present in an amount from about 66% to about 76% by weight.

26 (New). The composition of claim 1 comprising from about 0.2% to about 20% by weight of a hydroxide or salt of bis-(2-hydroxy-ethyl)-dimethyl ammonium and further comprising 2-(2-aminoethylamino)ethanol.

27(New). The composition of claim 1 further comprising 2-(2-aminoethylamino)ethanol.

28 (New). The composition of claim 17 comprising from about 0.2% to about 20% by weight of a hydroxide or salt of bis-(2-hydroxy-ethyl)-dimethyl ammonium.

29 (New). A cleaning or photoresist stripping composition comprising:

(a) a hydroxide and/or salt of bis-(2-hydroxy-ethyl)-dimethyl ammonium, a hydroxide and/or salt of tris-(2-hydroxy-ethyl)-methyl ammonium, or mixture thereof; and

(b) a cyclic nitrogen-containing solvent.

30 (New). A cleaning or photoresist stripping composition comprising:

(a) between 1% and 70% of a hydroxide and/or salt of bis-(2-hydroxy-ethyl)-dimethyl ammonium, a hydroxide and/or salt of tris-(2-hydroxy-ethyl)-methyl ammonium, or mixture thereof;

(b) water; and

(c) from about 0.2% to about 20% by weight of an amine, where the composition is free of polar organic solvents and of hydroxylamine

31 (New). A method of removing one or more of photoresist, etching residue, and flux material from an integrated circuit substrate, said method comprising:

a) providing an integrated circuit substrate comprising one or more of photoresist, etching residue, and flux material disposed on a surface thereof; and

b) contacting the surface with a composition of claim 1, wherein the surface is contacted by the composition for a time between 1 minute and 60 minutes and is at a temperature between 10° C and 100° C.

32 (New). A method of removing one or more of photoresist, etching residue, and flux material from an integrated circuit substrate, said method comprising:

a) providing an integrated circuit substrate comprising copper and a low-K material and having one or more of photoresist, etching residue, and flux material disposed on a surface thereof; and

b) contacting the surface with a composition of claim 29, wherein the surface is contacted by the composition for a time between 1 minute and 60 minutes and is at a temperature between 10° C and 100° C.

33 (New). A method of removing one or more of photoresist, etching residue, and flux material from an integrated circuit substrate, said method comprising:

a) providing an integrated circuit substrate comprising copper and a low-K material and having one or more of photoresist, etching residue, and flux material disposed on a surface thereof; and

b) contacting the surface with a composition of claim 30, wherein the surface is contacted by the composition for a time between 1 minute and 60 minutes and is at a temperature between 10° C and 100° C.